



#### 40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
40)/	$3.6$ m $\Omega$ @ $V_{GS} = 10V$	100A
40V	$5.2 \text{m}\Omega$ @ $V_{GS} = 5V$	90A

### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> Ensures On-State Losses are Minimized
- Excellent Q<sub>GD</sub> x R<sub>DS(ON)</sub> Product (FOM)
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMTH43M8LK3Q)

### **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

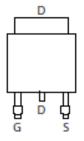
- Power Management Functions
- DC-DC Converters
- Backlighting

#### **Mechanical Data**

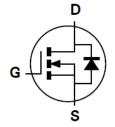
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (Approximate)







Pin Out Top View



**Equivalent Circuit** 

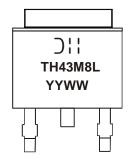
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH43M8LK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



TH43M8L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)

April 2017



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Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	40	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 5)	$T_A = +25$ °C $T_A = +100$ °C	I <sub>D</sub>	17.6 12.5	Α
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	$T_C = +25$ °C $T_C = +100$ °C	I <sub>D</sub>	100 80	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	150	Α
Maximum Continuous Body Diode Forward Current (Note 6)		Is	70	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I <sub>SM</sub>	150	Α
Avalanche Current, L=1mH		I <sub>AS</sub>	13.2	Α
Avalanche Energy, L=1mH		E <sub>AS</sub>	87	mJ

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	3.1	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	47	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	88	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	1.7	°C/W
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-55 to +175	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	2.9	3.6	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	4.3	5.2	mΩ	$V_{GS} = 5V, I_{D} = 15A$	
Diode Forward Voltage	$V_{SD}$	_	_	1.2	V	$V_{GS} = 0V, I_S = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>ISS</sub>	_	2,693	_		V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	1,172	_	pF		
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	52	_			
Gate Resistance	$R_{G}$	_	2.54	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_{G}$	_	38.5	_	nC		
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_G$	_	17.6	_		],, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	
Gate-Source Charge	$Q_{GS}$	_	6.9	_	nC	$V_{DS} = 20V, I_D = 20A$	
Gate-Drain Charge	$Q_{GD}$	_	6.9	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	5.2	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 20A, R_{G} = 1.6\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	5.7	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	23.5	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	11	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	35.4	_	ns	1 150 4:/4+ 1000/	
Body Diode Reverse Recovery Charge	$Q_{RR}$	_	32.9	_	nC	$I_F = 15A$ , di/dt = 100A/ $\mu$ s	

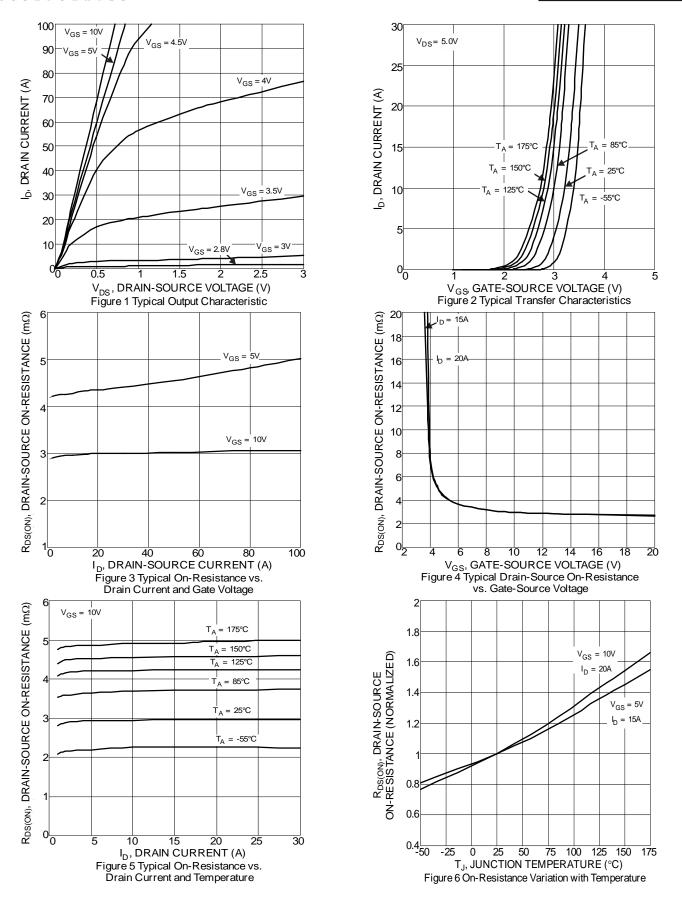
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. Notes:

6. Thermal resistance from junction to soldering point (on the exposed drain pad).

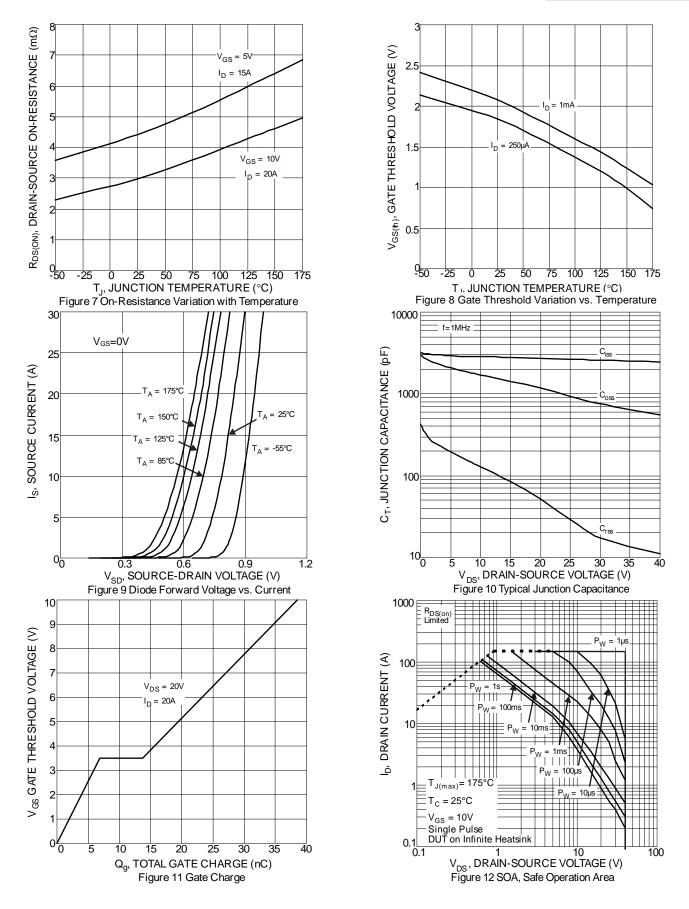
7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

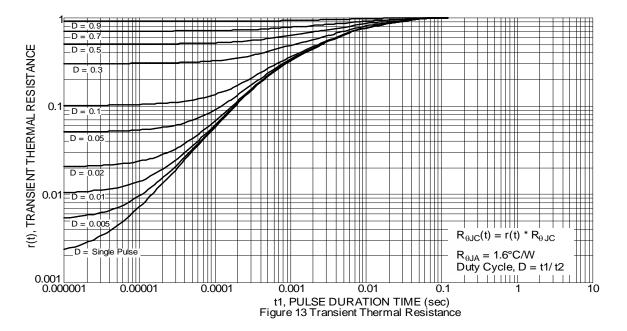








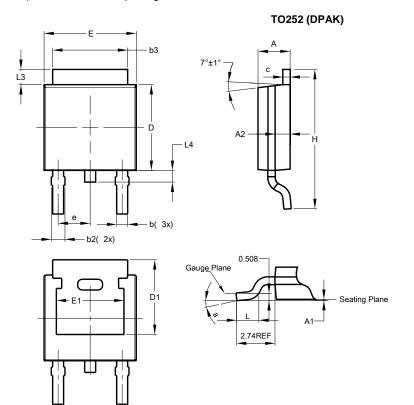






# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

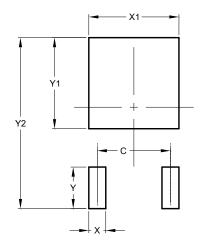


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
<b>A1</b>	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
q	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
Г	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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